**Product data sheet** 

## 1. General description

PNP low  $V_{CEsat}$  transistor in a SOT89 (SC-62/TO-243) small and flat lead Surface-Mounted Device (SMD) plastic package.

NPN complement: PBSS303NX

### 2. Features and benefits

- · Low collector-emitter saturation voltage VCEsat
- High collector current capability I<sub>C</sub> and I<sub>CM</sub>
- High collector current gain (h<sub>FE</sub>) at high I<sub>C</sub>
- · High efficiency due to less heat generation
- Smaller required Printed-Circuit Board (PCB) area than for conventional transistors
- AEC-Q101 qualified

## 3. Applications

- DC-to-DC conversion
- MOSFET gate driving
- Motor control
- Charging circuits
- · Power switches (e.g. motors, fans)

### 4. Quick reference data

Table 1. Quick reference data

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
V <sub>CEO</sub>	collector-emitter voltage	open base	-	-	-30	V
I <sub>C</sub>	collector current		-	-	-5.1	Α
I <sub>CM</sub>	peak collector current	single pulse; t <sub>p</sub> ≤ 1 ms	-	-	-10.2	Α
R <sub>CEsat</sub>	collector-emitter saturation resistance	$I_C$ = -4 A; $I_B$ = -200 mA; pulsed; $t_p \le$ 300 μs; $\delta \le$ 0.02; $T_{amb}$ = 25 °C	-	32	48	mΩ



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# 5. Pinning information

#### **Table 2. Pinning information**

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	Е	emitter		С
2	С	collector		, , , , , , , , , , , , , , , , , , ,
3	В	base	3 2 1	B—[
			SOT89	sym132

# 6. Ordering information

### **Table 3. Ordering information**

Type number			
	Name	Description	Version
PBSS303PX	SOT89	plastic, surface-mounted package; 3 leads; 1.5 mm pitch; 4.5 mm x 2.5 mm x 1.5 mm body	SOT89

# 7. Marking

### Table 4. Marking codes

Type number	Marking code[1]
PBSS303PX	%5K

[1] % = placeholder for manufacturing site code

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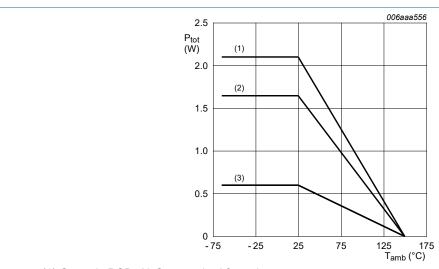
# 8. Limiting values

#### Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions		Min	Max	Unit
V <sub>CBO</sub>	collector-base voltage	open emitter		-	-30	V
V <sub>CEO</sub>	collector-emitter voltage	open base		-	-30	V
V <sub>EBO</sub>	emitter-base voltage	open collector		-	-5	V
Ic	collector current			-	-5.1	Α
I <sub>CM</sub>	peak collector current	single pulse; t <sub>p</sub> ≤ 1 ms		-	-10.2	Α
P <sub>tot</sub>	total power dissipation	T <sub>amb</sub> ≤ 25 °C	[1]	-	0.6	W
			[2]	-	1.65	W
			[3]	-	2.1	W
Tj	junction temperature			-	150	°C
T <sub>amb</sub>	ambient temperature			-65	150	°C
T <sub>stg</sub>	storage temperature			-65	150	°C

- Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint. Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for collector 6 cm<sup>2</sup>.
- Device mounted on a ceramic PCB, Al<sub>2</sub>O<sub>3</sub>, standard footprint. [3]



- (1) Ceramic PCB, Al<sub>2</sub>O<sub>3</sub>, standard footprint
- (2) FR4 PCB, mounting pad for collector 6 cm<sup>2</sup>
- (3) FR4 PCB, standard footprint

Fig. 1. **Power derating curves** 

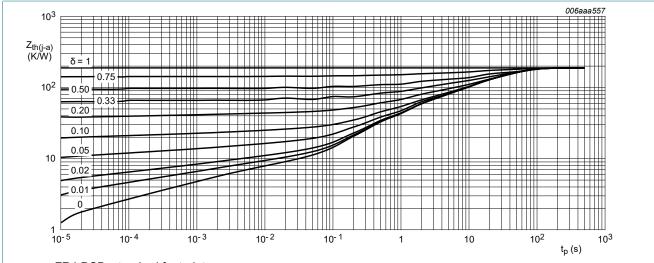
30 V, 5.1 A PNP low VCEsat transistor

### 9. Thermal characteristics

**Table 6. Thermal characteristics** 

Symbol	Parameter	Conditions		Min	Тур	Max	Unit
ui(j-a)	thermal resistance from junction to ambient	in free air	[1]	-	-	208	K/W
		-	[2]	-	-	76	K/W
			[3]	-	-	60	K/W
R <sub>th(j-sp)</sub>	thermal resistance from junction to solder point			-	-	20	K/W

- [1] Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.
- [2] Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for collector 6 cm<sup>2</sup>.
- [3] Device mounted on a ceramic PCB, Al<sub>2</sub>O<sub>3</sub>, standard footprint.



FR4 PCB, standard footprint

Fig. 2. Transient thermal impedance from junction to ambient as a function of pulse duration; typical values

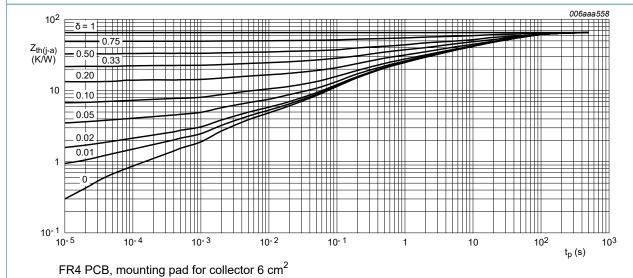
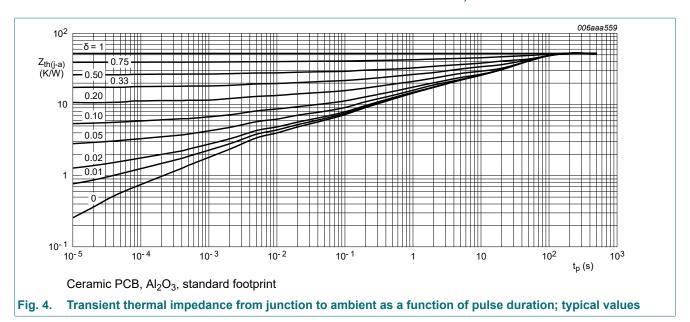


Fig. 3. Transient thermal impedance from junction to ambient as a function of pulse duration; typical values

### 30 V, 5.1 A PNP low VCEsat transistor



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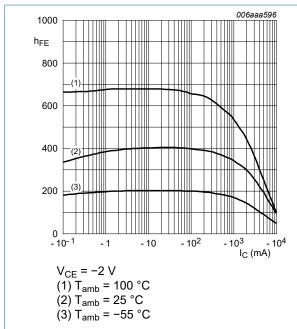
# 10. Characteristics

**Table 7. Characteristics** 

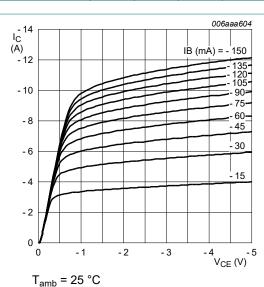
Symbol	Parameter	Conditions	Min	Тур	Max	Unit
I <sub>CBO</sub>	collector-base cut-off	$V_{CB} = -30 \text{ V}; I_{E} = 0 \text{ A}; T_{amb} = 25 \text{ °C}$	-	-	-100	nA
	current	$V_{CB} = -30 \text{ V}; I_E = 0 \text{ A}; T_j = 150 \text{ °C}$	-	-	-50	μΑ
ЕВО	emitter-base cut-off current	$V_{EB} = -5 \text{ V}; I_{C} = 0 \text{ A}; T_{amb} = 25 \text{ °C}$	-	-	-100	nA
h <sub>FE</sub>	DC current gain	$V_{CE}$ = -2 V; $I_{C}$ = -0.5 A; pulsed; $t_{p}$ ≤ 300 μs; δ ≤ 0.02; $T_{amb}$ = 25 °C	250	400	-	
		$V_{CE}$ = -2 V; $I_{C}$ = -1 A; pulsed; $t_{p}$ ≤ 300 μs; δ ≤ 0.02; $T_{amb}$ = 25 °C	250	370	-	
		$V_{CE}$ = -2 V; $I_{C}$ = -2 A; pulsed; $t_{p}$ ≤ 300 μs; δ ≤ 0.02; $T_{amb}$ = 25 °C	200	310	-	
		$V_{CE}$ = -2 V; $I_{C}$ = -4 A; pulsed; $t_{p}$ ≤ 300 μs; δ ≤ 0.02; $T_{amb}$ = 25 °C	150	220	-	
		$V_{CE}$ = -2 V; $I_{C}$ = -6 A; pulsed; $t_{p}$ ≤ 300 μs; δ ≤ 0.02; $T_{amb}$ = 25 °C	100	160	-	
V <sub>CEsat</sub>	collector-emitter saturation voltage	$I_C$ = -0.5 A; $I_B$ = -50 mA; pulsed; $t_p \le$ 300 μs; δ ≤ 0.02; $T_{amb}$ = 25 °C	-	-25	-35	mV
		$I_C$ = -1 A; $I_B$ = -50 mA; pulsed; $t_p \le$ 300 μs; δ ≤ 0.02; $T_{amb}$ = 25 °C	-	-50	-70	mV
		$I_C$ = -1 A; $I_B$ = -10 mA; pulsed; $t_p \le$ 300 μs; $\delta \le$ 0.02; $T_{amb}$ = 25 °C	-	-75	-105	mV
		$I_C$ = -2 A; $I_B$ = -40 mA; pulsed; $t_p \le$ 300 μs; δ ≤ 0.02; $T_{amb}$ = 25 °C	-	-90	-130	mV
		$I_C$ = -4 A; $I_B$ = -200 mA; pulsed; $t_p \le$ 300 μs; δ ≤ 0.02; $T_{amb}$ = 25 °C	-	-130	-190	mV
		$I_C$ = -4 A; $I_B$ = -400 mA; pulsed; $t_p \le$ 300 μs; δ ≤ 0.02; $T_{amb}$ = 25 °C	-	-120	-175	mV
		$I_C$ = -4 A; $I_B$ = -40 mA; pulsed; $t_p \le$ 300 μs; δ ≤ 0.02; $T_{amb}$ = 25 °C	-	-230	-350	mV
		$I_C$ = 5.1 A; $I_B$ = -255 mA; pulsed; $t_p \le$ 300 μs; δ ≤ 0.02; $T_{amb}$ = 25 °C	-	-160	-230	mV
R <sub>CEsat</sub>	collector-emitter saturation resistance	$I_C$ = -4 A; $I_B$ = -200 mA; pulsed; $t_p \le$ 300 μs; δ ≤ 0.02; $T_{amb}$ = 25 °C	-	32	48	mΩ
		$I_C$ = -4 A; $I_B$ = -40 mA; pulsed; $t_p \le$ 300 μs; δ ≤ 0.02; $T_{amb}$ = 25 °C	-	58	88	mΩ
/ <sub>BEsat</sub>	base-emitter saturation voltage	$I_C$ = -1 A; $I_B$ = -100 mA; pulsed; $t_p \le$ 300 μs; $\delta \le$ 0.02; $T_{amb}$ = 25 °C	-	-0.82	-0.9	V
		$I_C$ = -4 A; $I_B$ = -400 mA; pulsed; $t_p \le$ 300 μs; δ ≤ 0.02; $T_{amb}$ = 25 °C	-	-0.93	-1.05	V
/ <sub>BEon</sub>	base-emitter turn-on voltage	$V_{CE}$ = -2 V; $I_{C}$ = -2 A; pulsed; $t_{p}$ ≤ 300 μs; δ ≤ 0.02; $T_{amb}$ = 25 °C	-	-0.76	-0.85	V
d	delay time	$V_{CC} = -12.5 \text{ V}; I_C = -3 \text{ A}; I_{Bon} = -0.15 \text{ A};$	-	15	-	ns
г	rise time	I <sub>Boff</sub> = 0.15 A; T <sub>amb</sub> = 25 °C	-	55	-	ns
on	turn-on time			70	-	ns
s	storage time		-	215	-	ns
f	fall time		-	105	-	ns
off	turn-off time		-	320	-	ns

### 30 V, 5.1 A PNP low VCEsat transistor

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
f <sub>T</sub>	transition frequency	$V_{CE}$ = -10 V; $I_{C}$ = -0.1 A; f = 100 MHz; $T_{amb}$ = 25 °C	-	130	-	MHz
C <sub>c</sub>	collector capacitance	$V_{CB}$ = -10 V; $I_{E}$ = 0 A; $i_{e}$ = 0 A; $f$ = 1 MHz; $T_{amb}$ = 25 °C	-	110	160	pF



DC current gain as a function of collector Fig. 5. current; typical values



Collector current as a function of collector-Fig. 6. emitter voltage; typical values

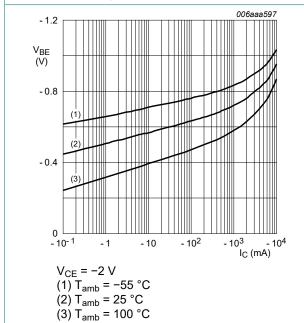
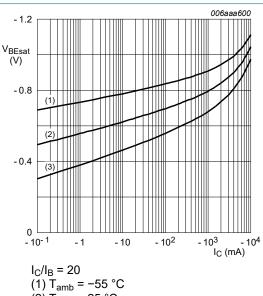


Fig. 7. Base-emitter voltage as a function of collector current; typical values



(2)  $T_{amb}$  = 25 °C (3)  $T_{amb}$  = 100 °C

Fig. 8. Base-emitter saturation voltage as a function of collector current; typical values

#### 30 V, 5.1 A PNP low VCEsat transistor

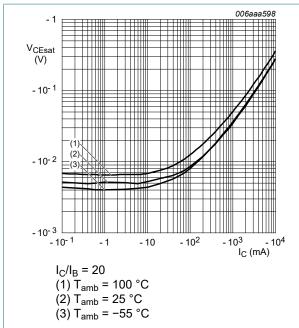


Fig. 9. Collector-emitter saturation voltage as a function of collector current; typical values

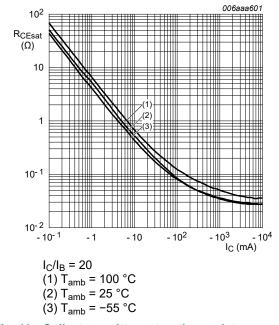


Fig. 11. Collector-emitter saturation resistance as a function of collector current; typical values

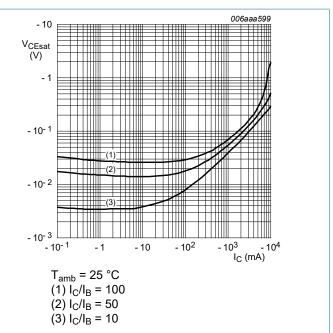


Fig. 10. Collector-emitter saturation voltage as a function of collector current; typical values

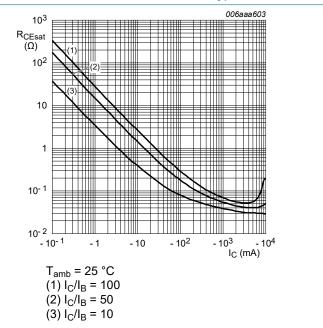
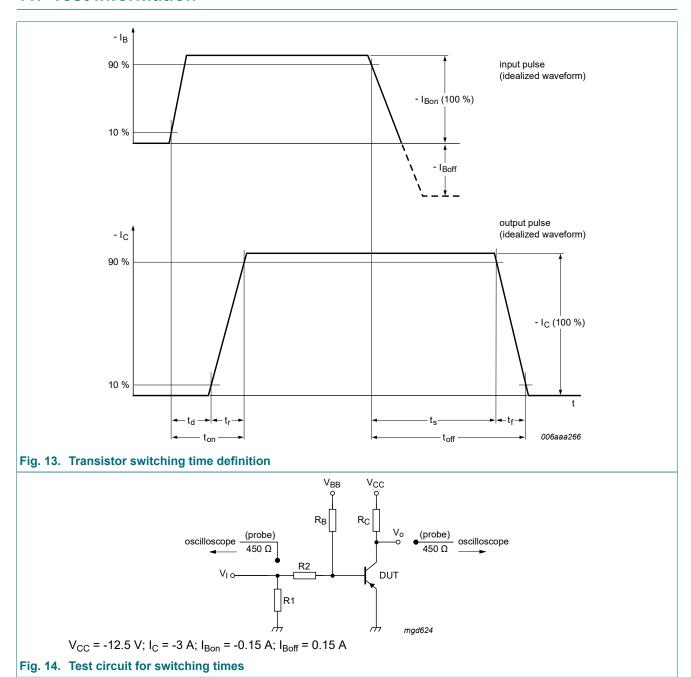


Fig. 12. Collector-emitter saturation resistance as a function of collector current; typical values

30 V, 5.1 A PNP low VCEsat transistor

## 11. Test information

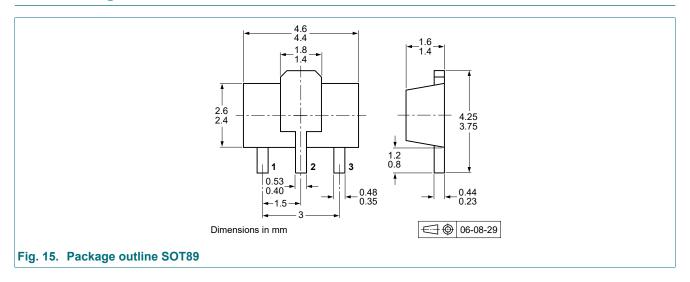


### **Quality information**

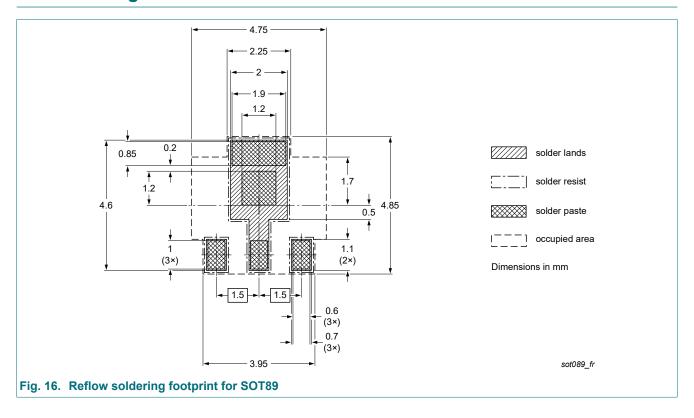
This product has been qualified in accordance with the Automotive Electronics Council (AEC) standard *Q101 - Stress test qualification for discrete semiconductors*, and is suitable for use in automotive applications.

30 V, 5.1 A PNP low VCEsat transistor

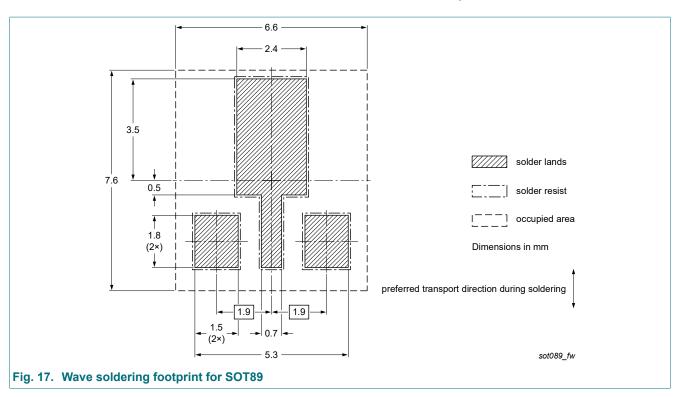
# 12. Package outline



# 13. Soldering



## 30 V, 5.1 A PNP low VCEsat transistor



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# 14. Revision history

#### **Table 8. Revision history**

Data sheet ID	Release date	Data sheet status	Change notice	Supersedes
PBSS303PX v.3	20240212	Product data sheet	-	PBSS303PX_2
Modifications:	Nexperia. • Legal texts ha	this data sheet has been rede ve been adapted to the new o ing information" removed.		
PBSS303PX_2	20091120	Product data sheet	-	PBSS303PX_1
PBSS303PX_1	20060822	Product data sheet	-	-

#### 30 V, 5.1 A PNP low VCEsat transistor

### 15. Legal information

#### **Data sheet status**

Document status [1][2]	Product status [3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

- Please consult the most recently issued document before initiating or completing a design.
- [2] The term 'short data sheet' is explained in section "Definitions".
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### 30 V, 5.1 A PNP low VCEsat transistor

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For more information, please visit: http://www.nexperia.com For sales office addresses, please send an email to: salesaddresses@nexperia.com Date of release: 12 February 2024

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